

Yuan-Ming Chang

List of Publications by Year in descending order

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14
papers

424
citations

840776

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docs citations

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times ranked

821
citing authors

#	ARTICLE	IF	CITATIONS
1	High Mobilities in Layered InSe Transistors with Indium-Encapsulation-Induced Surface Charge Doping. <i>Advanced Materials</i> , 2018, 30, e1803690.	21.0	101
2	Oxidation-boosted charge trapping in ultra-sensitive van der Waals materials for artificial synaptic features. <i>Nature Communications</i> , 2020, 11, 2972.	12.8	83
3	Reversible and Precisely Controllable p/n-Type Doping of MoTe ₂ Transistors through Electrothermal Doping. <i>Advanced Materials</i> , 2018, 30, e1706995.	21.0	68
4	Analog Circuit Applications Based on All-2D Ambipolar ReSe ₂ Field-Effect Transistors. <i>Advanced Functional Materials</i> , 2019, 29, 1809011.	14.9	36
5	Multifunctional full-visible-spectrum optoelectronics based on a van der Waals heterostructure. <i>Nano Energy</i> , 2019, 66, 104107.	16.0	28
6	Two-dimensional MoTe ₂ materials: From synthesis, identification, and charge transport to electronics applications. <i>Japanese Journal of Applied Physics</i> , 2016, 55, 1102A1.	1.5	20
7	Negative-Differential-Resistance Devices Achieved by Band-Structure Engineering in Silicene under Periodic Potentials. <i>Physical Review Applied</i> , 2018, 10, .	3.8	19
8	Defect Engineering in Ambipolar Layered Materials for Mode-Regulable Nociceptor. <i>Advanced Functional Materials</i> , 2021, 31, 2007587.	14.9	19
9	Atomically thin van der Waals tunnel field-effect transistors and its potential for applications. <i>Nanotechnology</i> , 2019, 30, 105201.	2.6	17
10	Broadband Omnidirectional Light Trapping in Gold-Decorated ZnO Nanopillar Arrays. <i>ACS Applied Materials & Interfaces</i> , 2017, 9, 11985-11992.	8.0	13
11	Oxygen-Sensitive Layered MoTe ₂ Channels for Environmental Detection. <i>ACS Applied Materials & Interfaces</i> , 2019, 11, 47047-47053.	8.0	13
12	Facile and Reversible Carrier-Type Manipulation of Layered MoTe ₂ Toward Long-Term Stable Electronics. <i>ACS Applied Materials & Interfaces</i> , 2020, 12, 42918-42924.	8.0	4
13	A Triode Device with a Gate Controllable Schottky Barrier: Germanium Nanowire Transistors and Their Applications. <i>Small</i> , 2019, 15, 1900865.	10.0	2
14	Probing Charge Transport Difference in Parallel and Vertical Layered Electronics with Thin Graphite Source/Drain Contacts. <i>Scientific Reports</i> , 2019, 9, 20087.	3.3	1